

Notice of References Cited

Application/Control No.

09/536,927

Applicant(s)/Patent Under

Reexamination

HAWRYLUK ET AL.

Examiner

Toniae M. Thomas

Art Unit

2822

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,238,587 B1	05-2001	Siniaguine et al.	216/59
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kramer et al., "Characterization of Reverse Leakage Components for Ultrashallow p+/n Diodes Fabricated Using Gas Immersion Laser Doping," IEEE Electron Device Letters, Vol. 17, No. 10, October 1996, pages 461-463.
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
 Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.